

# Michael Hanke

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Scanning x-ray microscopy: A sub-100 nm probe toward strain and composition in seeded horizontal Ge(110) nanowires. <i>Applied Physics Letters</i> , 2022, 120, 101902.	3.3	0
2	Elastic behavior of metal-assisted etched Si/SiGe superlattice nanowires containing dislocations. <i>AIP Advances</i> , 2022, 12, 045006.	1.3	0
3	Temperature dependence of three-dimensional domain wall arrangement in ferroelectric K <sub>0.9</sub> Na <sub>0.1</sub> NbO <sub>3</sub> epitaxial thin films. <i>Journal of Applied Physics</i> , 2020, 128, .	2.5	8
4	Ferroelectric phase transitions in multi-domain K <sub>0.9</sub> Na <sub>0.1</sub> NbO <sub>3</sub> epitaxial thin films. <i>Nano Futures</i> , 2020, 4, 035005.	2.2	4
5	Hierarchy and scaling behavior of multi-rank domain patterns in ferroelectric K <sub>0.9</sub> Na <sub>0.1</sub> NbO <sub>3</sub> strained films. <i>Nanotechnology</i> , 2018, 29, 015701.	2.6	12
6	Thermal expansion of single-crystalline $\langle i \rangle \hat{1}^2 \langle /i \rangle$ -Ga <sub>2</sub> O <sub>3</sub> from RT to 1200 K studied by synchrotron-based high resolution x-ray diffraction. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	15
7	Growth mode evolution during (100)-oriented $\langle i \rangle \hat{1}^2 \langle /i \rangle$ -Ga <sub>2</sub> O <sub>3</sub> homoepitaxy. <i>Nanotechnology</i> , 2018, 29, 395705.	2.6	12
8	Structure and Composition of Isolated Core-Shell $\text{mml:math}$ $\text{xmlns:mml}=\text{"http://www.w3.org/1998/Math/MathML"} \text{ display}=\text{"inline"} <\text{mml:mrow}> <\text{mml:mo stretchy}=\text{"false"}> </\text{mml:mo}> <\text{mml:mi}> \text{In} </\text{mml:mi}> <\text{mml:mo}>, </\text{mml:mo}> <\text{mml:mi}> \text{Ga} </\text{mml:mi}> <\text{mml:mo}> \text{Tj ETQq0 0 0 rgBT /Overl} <\text{mml:math variant}=\text{"normal"}> \text{N} </\text{mml:mi}> <\text{mml:mo}>/ </\text{mml:mo}> <\text{mml:mi}> \text{GaN} </\text{mml:mi}> </\text{mml:mrow}> </\text{mml:math}> \text{Rods}$ Based on Nanofocus X-Ray Diffraction and Scanning Transmission Electron Microscopy. <i>Physical Review</i>	3.8	12
9	Influence of strain relaxation in axial $\text{In}_x\text{GaN}_{1-x}$ nanowire heterostructures on their electronic properties. <i>Nanotechnology</i> , 2017, 28, 215204.	2.6	2
10	Strain engineering of monoclinic domains in K $\langle i \rangle \text{x} \langle /i \rangle$ Na $\langle sub \rangle 1\hat{\wedge} \langle i \rangle \text{x} \langle /i \rangle$ NbO $\langle sub \rangle 3 \langle /sub \rangle$ epitaxial layers: a pathway to enhanced piezoelectric properties. <i>Nanotechnology</i> , 2017, 28, 24LT02.	2.6	22
11	Phase formation and strain relaxation of Ga <sub>2</sub> O <sub>3</sub> on c-plane and a-plane sapphire substrates as studied by synchrotron-based x-ray diffraction. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	58
12	Strain Engineering of Ferroelectric Domains in K $x\text{Na}1\hat{\wedge} x\text{NbO}_3$ Epitaxial Layers. <i>Frontiers in Materials</i> , 2017, 4, .	2.4	27
13	Counterintuitive strain distribution in axial (In,Ga)N/GaN nanowires. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	14
14	Strain dynamics during La <sub>2</sub> O <sub>3</sub> /Lu <sub>2</sub> O <sub>3</sub> superlattice and alloy formation. <i>Journal of Applied Physics</i> , 2016, 119, 215301.	2.5	1
15	Nanofocus x-ray diffraction and cathodoluminescence investigations into individual core-shell (In,Ga)N/GaN rod light-emitting diodes. <i>Nanotechnology</i> , 2016, 27, 325707.	2.6	18
16	Delayed crystallization of ultrathin Gd <sub>2</sub> O <sub>3</sub> layers on Si(111) observed by in situ X-ray diffraction. <i>Nanoscale Research Letters</i> , 2012, 7, 203.	5.7	14